

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1301	(strip or stripped or stripping or etch or etching or etched) adj10 ((hard adj mask) or (silicon adj nitride) or (silicon adj oxynitride) or SiN or SiON) adj10 (resist or resists or photoresist or photoresists or BARC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/13 08:29
2	BRS	L2	277	(strip or stripped or stripping or etch or etching or etched) adj3 ((hard adj mask) or (silicon adj nitride) or (silicon adj oxynitride) or SiN or SiON) adj3 (resist or resists or photoresist or photoresists or BARC)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/13 09:07
3	BRS	L3	93	2 and (plasma adj etch\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/13 08:52
4	BRS	L4	114	(pattern or patterned or patterning) adj3 (hard adj mask) adj7 (hole or holes or trench or trenches or aperture or apertures or via or vias or gap or gaps)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/13 09:08

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	167	(438/9) .CCLS.	USPAT
2	IS&R	L2	569	(438/694) .CCLS.	USPAT
3	IS&R	L3	264	(438/695) .CCLS.	USPAT
4	IS&R	L4	50	(438/709) .CCLS.	USPAT